

PJP10NA80 / PJF10NA80

800V N-Channel MOSFET

Voltage

800 V

Current

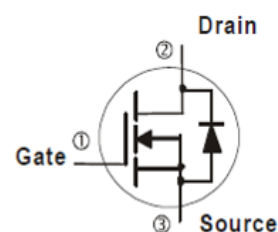
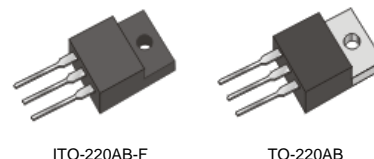
10 A

Features

- $R_{DS(ON)}$, $V_{GS}@10V, I_D@5A < 1.15\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std.
(Halogen Free)

Mechanical Data

- Case: TO-220AB, ITO-220AB-F Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- TO-220AB Approx. Weight : 0.067 ounces, 1.89 grams
- ITO-220AB-F Approx. Weight : 0.068 ounces, 2 grams



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER		SYMBOL	TO-220AB	ITO-220AB-F	UNITS
Drain-Source Voltage		V_{DS}	800		V
Gate-Source Voltage		V_{GS}	± 30		V
Continuous Drain Current		I_D	10		A
Pulsed Drain Current		I_{DM}	40		A
Single Pulse Avalanche Energy (Note 1)		E_{AS}	795		mJ
Power Dissipation	$T_C=25^\circ\text{C}$	P_D	180	60	W
	Derate above 25°C		1.44	0.48	W/ $^\circ\text{C}$
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150		$^\circ\text{C}$
Typical Thermal resistance					
- Junction to Case		$R_{\theta JC}$	0.69	2.08	$^\circ\text{C}/\text{W}$
- Junction to Ambient		$R_{\theta JA}$	62.5	120	

- Limited only By Maximum Junction Temperature



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Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	800	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	2	3	4	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =5A	-	1.05	1.15	Ω
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =800V, V _{GS} =0V	-	0.01	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V	-	±10	±100	nA
Diode Forward Voltage	V _{SD}	I _S =10A, V _{GS} =0V	-	0.87	1.4	V
Dynamic (Note 4)						
Total Gate Charge	Q _g	V _{DS} =640V, I _D =10A, V _{GS} =10V (Note 2,3)	-	31	-	nC
Gate-Source Charge	Q _{gs}		-	8	-	
Gate-Drain Charge	Q _{gd}		-	12	-	
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1.0MHZ	-	1517	-	pF
Output Capacitance	C _{oss}		-	180	-	
Reverse Transfer Capacitance	C _{rss}		-	9	-	
Turn-On Delay Time	td _(on)	V _{DD} =400V, I _D =10A, R _G =25Ω (Note 2,3)	-	22	-	ns
Turn-On Rise Time	t _r		-	31	-	
Turn-Off Delay Time	td _(off)		-	56	-	
Turn-Off Fall Time	t _f		-	31	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I _S	---	-	-	10	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}	---	-	-	40	A
Reverse Recovery Time	trr	V _{GS} =0V, I _S =10A	-	660	-	ns
Reverse Recovery Charge	Qrr	dl _F / dt=100A/us (Note 2)	-	6	-	uC

NOTES :

1. $L=30\text{mH}, I_{AS}=7.1A, V_{DD}=50V, R_G=25\text{ohm}$, Starting $T_J=25^{\circ}\text{C}$
2. Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
3. Essentially independent of operating temperature typical characteristics.
4. Guaranteed by design, not subject to production testing

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TYPICAL CHARACTERISTIC CURVES

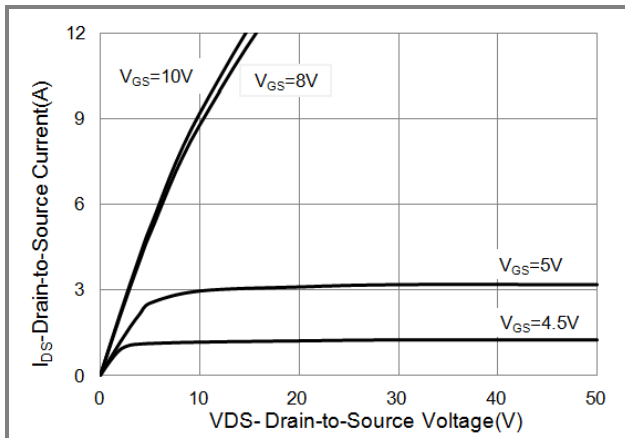


Fig.1 Output Characteristics

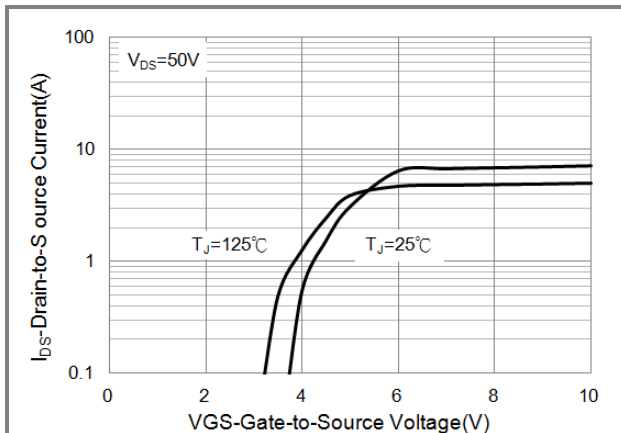


Fig.2 Transfer Characteristics

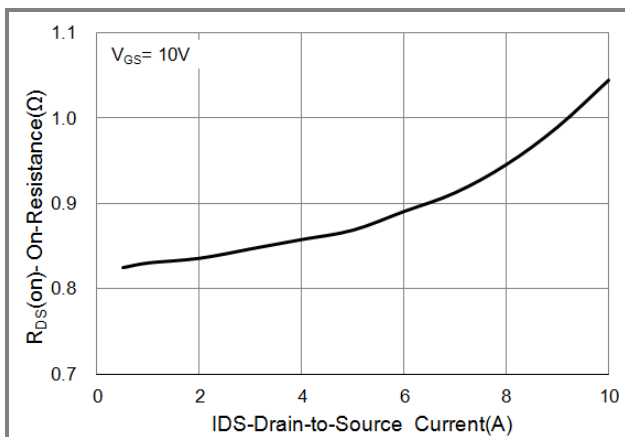


Fig.3 On-Resistance vs. Drain Current

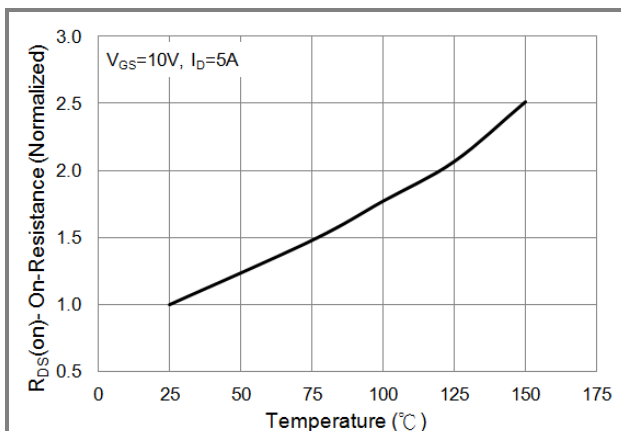


Fig.4 On-Resistance vs. Junction temperature

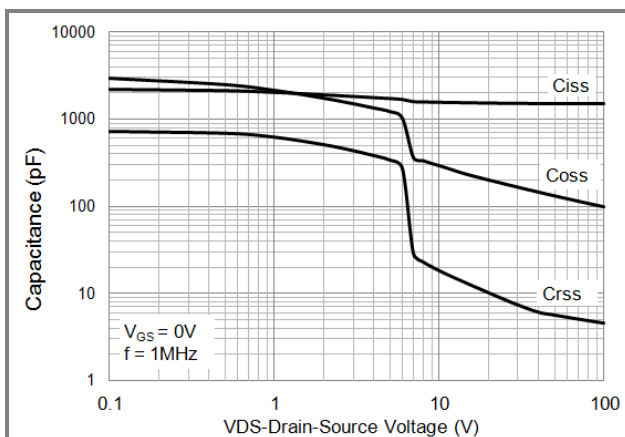


Fig.5 Capacitance vs. Drain-Source Voltage

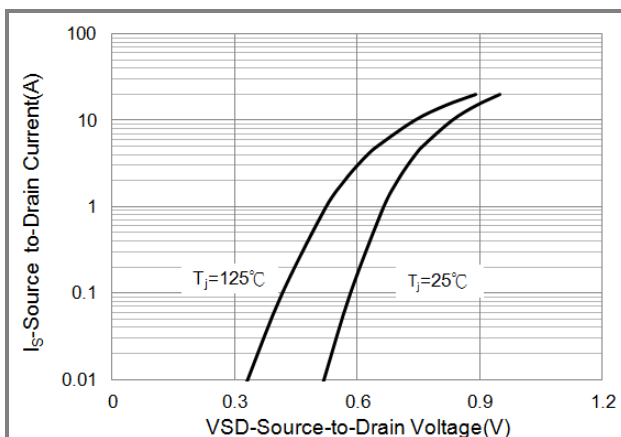


Fig.6 Body Diode Characteristics

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TYPICAL CHARACTERISTIC CURVES

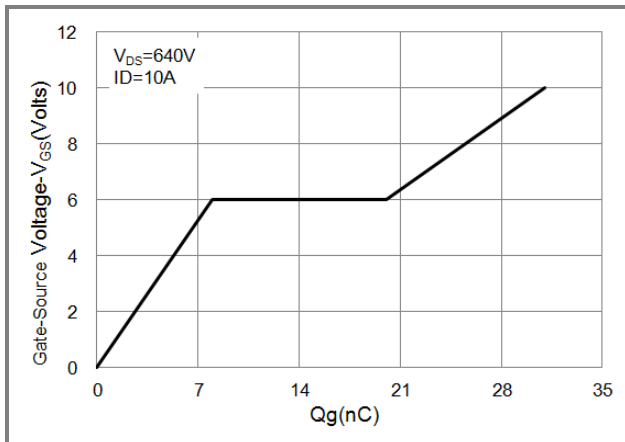


Fig.7 Gate-Charge Characteristics

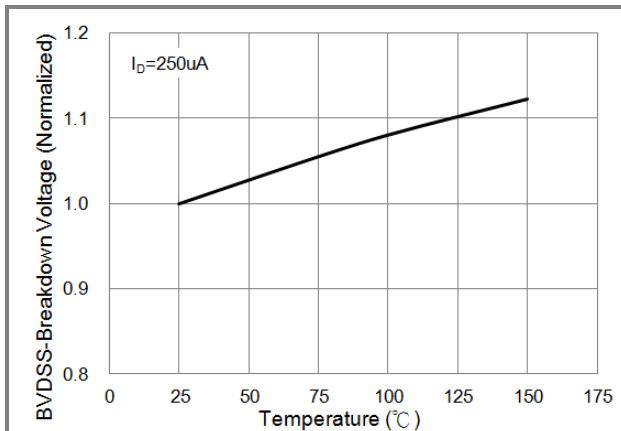


Fig.8 Breakdown Voltage Variation vs. Temperature

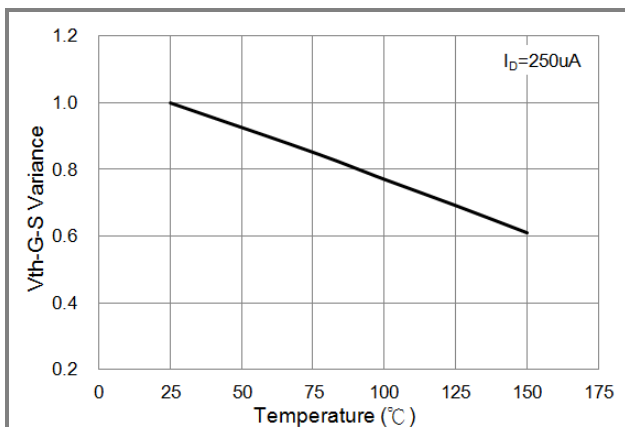


Fig.9 Threshold Voltage Variation with Temperature

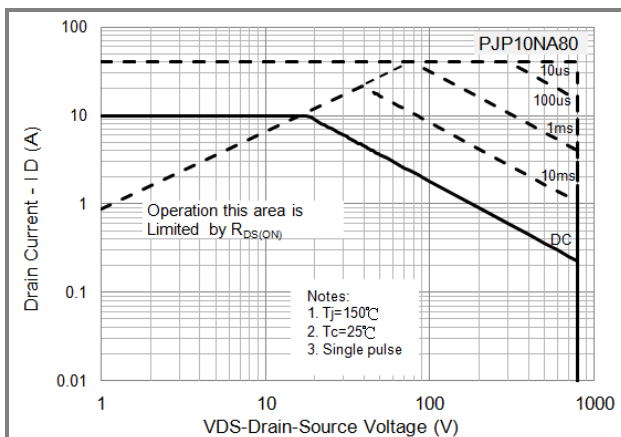


Fig.10 Maximum Safe Operating Area

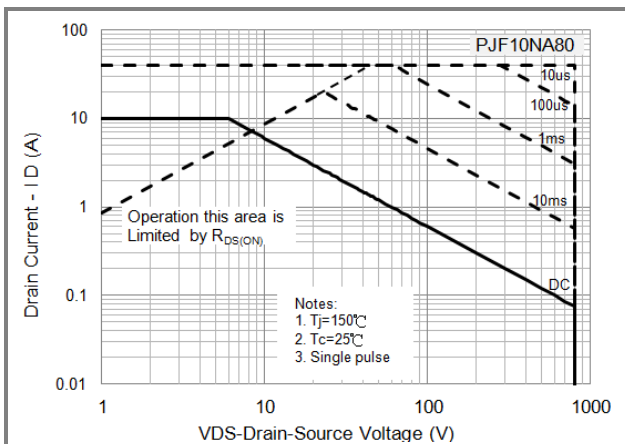


Fig.11 Maximum Safe Operating Area

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TYPICAL CHARACTERISTIC CURVES

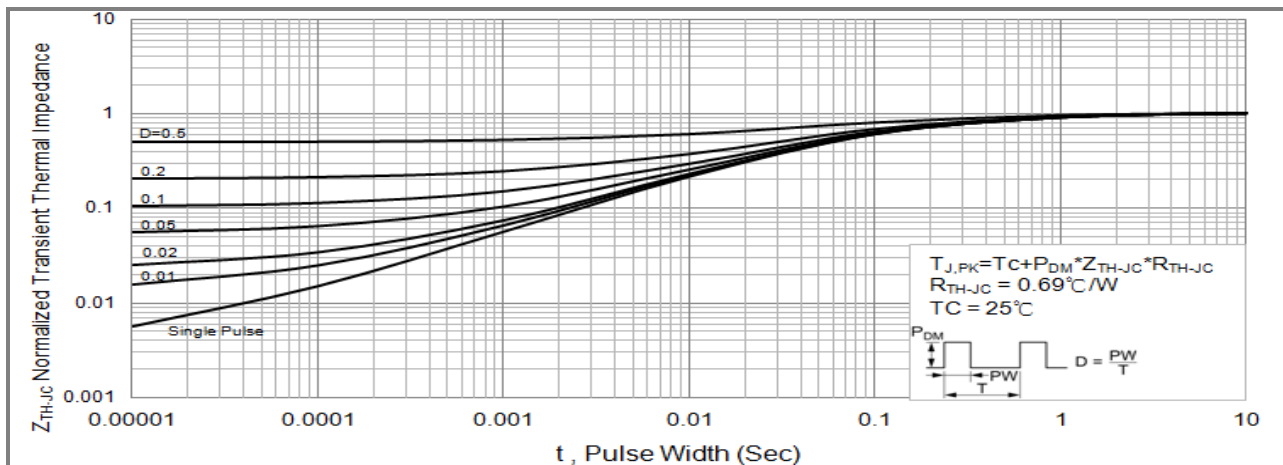


Fig.13 PJP10NA80 Normalized Transient Thermal Impedance vs. Pulse Width

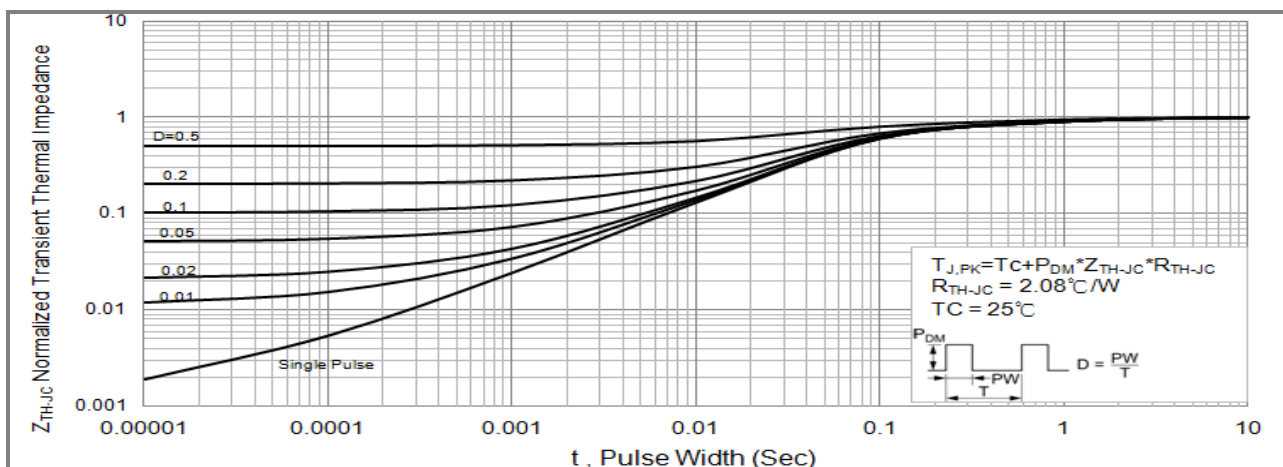
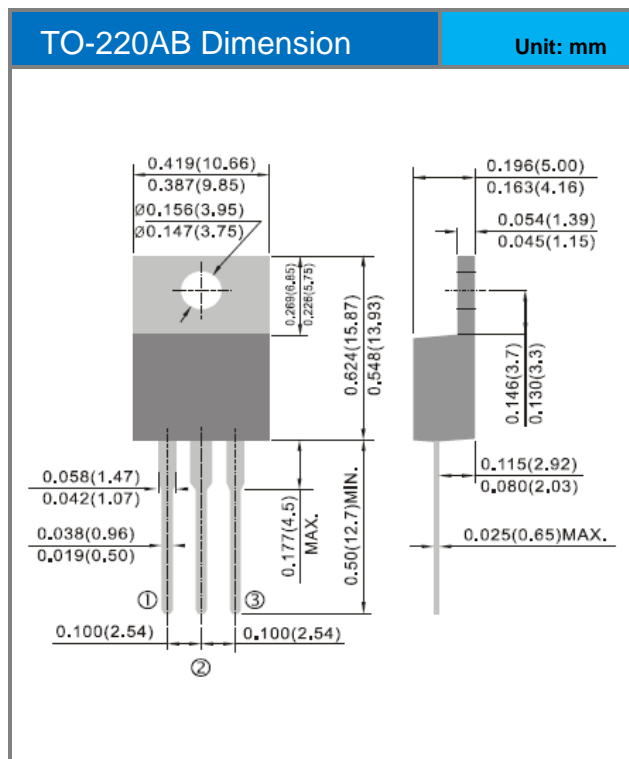
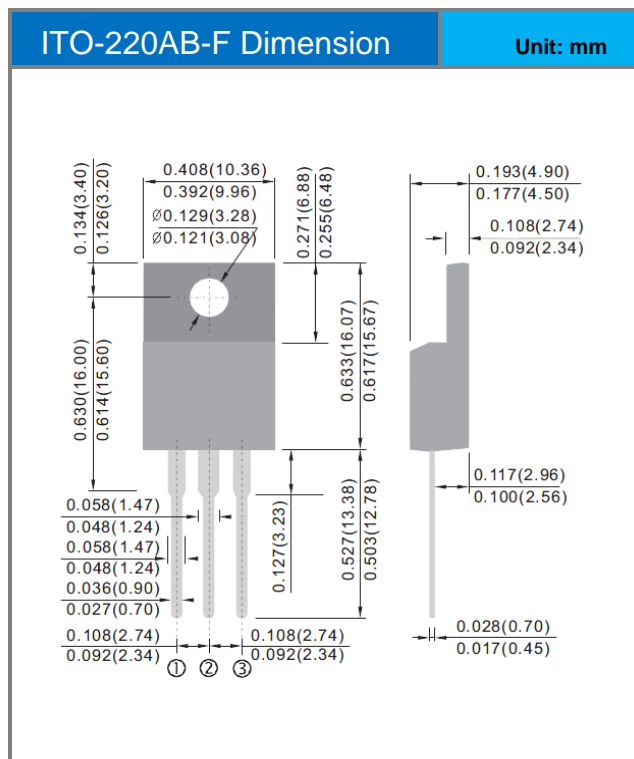


Fig.14 PJF10NA80 Normalized Transient Thermal Impedance vs. Pulse Width

PJP10NA80 / PJF10NA80

Packaging Information





PJP10NA80 / PJF10NA80

PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJP10NA80_T0_00001	TO-220AB	50pcs / Tube	P10NA80	Halogen free
PJF10NA80_T0_00001	ITO-220AB-F	50pcs / Tube	F10NA80	Halogen free



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